

forming a conductive layer pattern and an insulating film spacer on a sidewall of said conductive layer pattern through a common process;

removing said insulating film spacer in a region other than a contact plug formation region; and

forming an interlayer dielectric film on an entire surface of the semiconductor device.

4. (Amended) The method according to claim 3, wherein said conductive layer pattern comprises one of a word line and a bit line.

5. (Amended) A method of forming an interlayer dielectric film in a semiconductor device, the method comprising:

forming conductive layer patterns of a given pattern through a common process;

forming an interlayer dielectric film on an entire surface of the semiconductor device;

removing said interlayer dielectric film at a contact plug formation region; and

forming an insulating film spacer on a sidewall of said conductive layer patterns.

6. (Amended) The method according to claim 5, wherein at least one of said conductive layer patterns comprises one of a word line and a bit line.

7. (Amended) A method of forming an interlayer dielectric film in a semiconductor device, the method comprising:

forming conductive layer patterns and an insulating film spacer on a sidewall of said conductive layer patterns through a common process;

burying a conductive material between said conductive layer patterns;

removing said conductive material at a removal region such that said conductive material remains at remaining regions to form a contact plug; and

burying an interlayer dielectric film between said conductive layer patterns at said removal region.

8. (Amended) The method according to claim 7, wherein at least one of said conductive layer patterns comprises one of a word line and a bit line.